

L Number	Hits	Search Text	DB	Time stamp
-	5644	((438/787-788) or (438/694) or (438/700) or (438/702) or (438/976)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 15:31
-	0	((438/787-788) or (438/694) or (438/700) or (438/702) or (438/976)).CCLS.) and LCD and ((via or trench or opening or plug) same protective same oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 09:40
-	5	((438/787-788) or (438/694) or (438/700) or (438/702) or (438/976)).CCLS.) and LCD and ((via or trench or opening or plug) same oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 09:40
-	59	((438/787-788) or (438/694) or (438/700) or (438/702) or (438/976)).CCLS.) and ((via or trench or opening or plug) same protective same oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 13:20
-	0	((438/787-788) or (438/694) or (438/700) or (438/702) or (438/976)).CCLS.) and ((via or trench or opening or plug) same prottrochchengianieective same oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 13:13
-	0	serrocchengiani	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 13:20
-	1923	semiconductor and (via or plug or contact or hole) and gate and LCD and (photoresist or resist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 13:22
-	178	semiconductor and (via or plug or contact or hole) and gate and LCD and ((photoresist or resist) with remov\$4 same wet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 13:41
-	342	semiconductor and (photoresist or resist).ti. and LCD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 13:53
-	135	semiconductor and (photoresist).ti. and LCD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 14:15
-	21	semiconductor and (photoresist with remov\$4 with protect\$4).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 14:19
-	88	semiconductor and (photoresist with overetch)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 14:33
-	384	semiconductor and ((via or contact or plug or hole) with treatment).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 14:55

-	7	(semiconductor and ((via or contact or plug or hole) with treatment).ti.) and LCD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 14:35
-	6	(semiconductor and ((via or contact or plug or hole) with treatment).ti.) and UV	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 14:35
-	0	(semiconductor and ((via or contact or plug or hole) with treatment).ti.) and sacrificial	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 14:36
-	30	(semiconductor and ((via or contact or plug or hole) with treatment).ti.) and (fill or filling)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 14:56
-	402	semiconductor and ((trench or via or contact or plug or hole) with treatment).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 14:56
-	7	(semiconductor and ((trench or via or contact or plug or hole) with treatment).ti.) and LCD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 14:56
-	6	(semiconductor and ((trench or via or contact or plug or hole) with treatment).ti.) and UV	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 14:56
-	36	(semiconductor and ((trench or via or contact or plug or hole) with treatment).ti.) and (fill or filling)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 14:56
-	6	((semiconductor and ((trench or via or contact or plug or hole) with treatment).ti.) and (fill or filling)) not ((semiconductor and ((via or contact or plug or hole) with treatment).ti.) and (fill or filling))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 15:11
-	0	semiconductor and (SiN same ILD) and ((photoresist or resist) with strip) and (metal with contact with oxidiz\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 15:13
-	0	semiconductor and (SiN same ILD) and ((photoresist or resist) with strip) and (native with oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 15:13
-	137	semiconductor and (trench or via or contact or hole) and ((photoresist or resist) with strip) and (native with oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 15:14
-	1298	semiconductor and (trench or via or contact or hole) and ((photoresist or resist) with (strip\$4 or remov\$4)) and (native with oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 15:14
-	40059	(semiconductor and (trench or via or contact or hole) and ((photoresist or resist) with (strip\$4 or remov\$4)) and (native with oxide)) (wet with etch\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 15:14

-	71	(semiconductor and (trench or via or contact or hole) and ((photoresist or resist) with (strip\$4 or remov\$4)) and (native with oxide)) and (wet with etch\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 15:31
-	2390	(438/637-640).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 15:31
-	860	((438/637-640).CCLS.) and ((metal with oxide) or (native with oxide) or (protective with oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 15:32
-	646	((438/637-640).CCLS.) and ((metal with oxide) or (native with oxide) or (protective with oxide))) and (resist or photoresist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 15:33
-	5	((438/637-640).CCLS.) and ((metal with oxide) or (native with oxide) or (protective with oxide))) and (resist or photoresist)) and LCD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 15:37
-	325	semiconductor and (MIMS or MUMS)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/22 16:59
-	248	(semiconductor and (MIMS or MUMS)) and (trench or via or contact or hole)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/22 17:03
-	13559	semiconductor and ((treat or treatment or treated) with (trench or via or contact or hole))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/22 17:04
-	336	(semiconductor and ((treat or treatment or treated) with (trench or via or contact or hole))) and sacrificial	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/22 17:04
-	194	((semiconductor and ((treat or treatment or treated) with (trench or via or contact or hole))) and sacrificial) and (photoresist or resist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/22 17:10
-	153	rocchegiani	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/22 17:10
-	17	rocchegiani and damascene	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/22 17:11
-	14	("5821169" "5877075" "5882996" "5895253" "6025277" "6057239" "6100184" "6136680" "6153511" "6177364" "6204168" "6211061" "6294457" "6297149").PN.	USPAT	2003/08/22 17:13
-	1	6380073.URPN.	USPAT	2003/08/22 17:15

-	21	semiconductor and (IC or interconnect) and (via or hole or contact or plug or trench) same (treat\$4 same passivat\$4 same ((photoresist or resist) with (strip\$3 or remov\$4)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/27 10:55
-	154	rocchegiani	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/27 10:56
-	62	rocchegiani and (via or damascene)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/27 11:22
-	12	("4356374" "4793201" "5266521" "5407855" "5523177" "5561082" "5585673" "5670421" "5731634" "5846673" "5969422" "6002174").PN.	USPAT	2003/08/27 11:13
-	14134	(IC or (integrated with circuit)) and ((via or trench or contact) same treat\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/27 11:23
-	3003	((IC or (integrated with circuit)) and ((via or trench or contact) same treat\$4)) and ((photoresist or resist) with (remove or removing or removal or strip or stripping or stripped or etch or etching or etched or ash or ashed or ashing))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/27 11:26
-	824	((IC or (integrated with circuit)) and ((via or trench or contact) same treat\$4)) and ((photoresist or resist) with (remove or removing or removal or strip or stripping or stripped or etch or etching or etched or ash or ashed or ashing))) and (UV or (ultraviolet))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/27 11:26
-	309	((IC or (integrated with circuit)) and ((via or trench or contact) same treat\$4)) and ((photoresist or resist) with (remove or removing or removal or strip or stripping or stripped or etch or etching or etched or ash or ashed or ashing))) and (UV or (ultraviolet))) and (wet with etch\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/27 15:36
-	478	semiconductor and (dielectric adj mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/27 16:29
-	6	(semiconductor and (dielectric adj mask)) and (wet adj etch\$4 with (photoresist or resist))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/27 16:33
-	3429	(438/694).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/27 16:33
-	249	((438/694).CCLS.) and trench\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/28 09:35
-	5	("5494860" "5814557" "5925933" "6030895" "6184121").PN.	USPAT	2003/08/28 09:25

-	0	semiconductor and (UV with anneal with contact)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/28 10:44
-	61	semiconductor and (UV with anneal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/28 10:48
-	2205	semiconductor and ((photoresist or resist) with remov\$5).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/28 10:49
-	497	(semiconductor and ((photoresist or resist) with remov\$5).ti.) and (trench or via or contact or hole or plug)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/28 10:49
-	51	((semiconductor and ((photoresist or resist) with remov\$5).ti.) and (trench or via or contact or hole or plug)) and (UV or ultraviolet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/28 12:58
-	82	(438/976).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/28 15:04
-	729	semiconductor and (interconnect) and (treatment with (via or contact or trench or plug))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/28 15:54
-	423	(semiconductor and (interconnect) and (treatment with (via or contact or trench or plug))) and (photoresist or resist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/28 15:31
-	1	((semiconductor and (interconnect) and (treatment with (via or contact or trench or plug))) and (photoresist or resist)) and ((UV or ultraviolet) same plasma with (oxidation or oxidize or oxidized))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/28 15:33
-	1	((semiconductor and (interconnect) and (treatment with (via or contact or trench or plug))) and (photoresist or resist)) and ((UV or ultraviolet) same (oxidation or oxidize or oxidized))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/28 15:33
-	223	((semiconductor and (interconnect) and (treatment with (via or contact or trench or plug))) and (photoresist or resist)) and ((oxidation or oxidize or oxidized))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/28 15:33
-	10	semiconductor and (interconnect) and (UV with treatment with (via or contact or trench or plug))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/28 15:55
-	11	semiconductor and (interconnect) and (oxidation with treatment with (via or contact or trench or plug))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/28 15:56
-	0	(LCD or (liquid adj crystal adj display)) and (bus adj line) and (driving with transistor with (source or drain)) and polysilicon and (gate with metal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 11:18

-	0	(LCD or (liquid adj crystal adj display)) and (bus adj line) and (transistor with (source or drain)) and polysilicon and (gate with metal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/03 11:18
-	15	(LCD or (liquid adj crystal adj display)) and (bus adj line) and (driving with transistor with (source or drain)) and polysilicon and (gate with metal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/03 11:18
-	0	((LCD or (liquid adj crystal adj display)) and (bus adj line) and (driving with transistor with (source or drain)) and polysilicon and (gate with metal)) and (damascene)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/03 11:18
-	14	((LCD or (liquid adj crystal adj display)) and (bus adj line) and (driving with transistor with (source or drain)) and polysilicon and (gate with metal)) and (trench or via or hole or contact)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/03 11:19